

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	GS1A THRU GS1M
▶ Overseas	Part Number	GS1A THRU GS1M
▶ Equivalent	Part Number	GS1A THRU GS1M

EV is the abbreviation of name EVVO

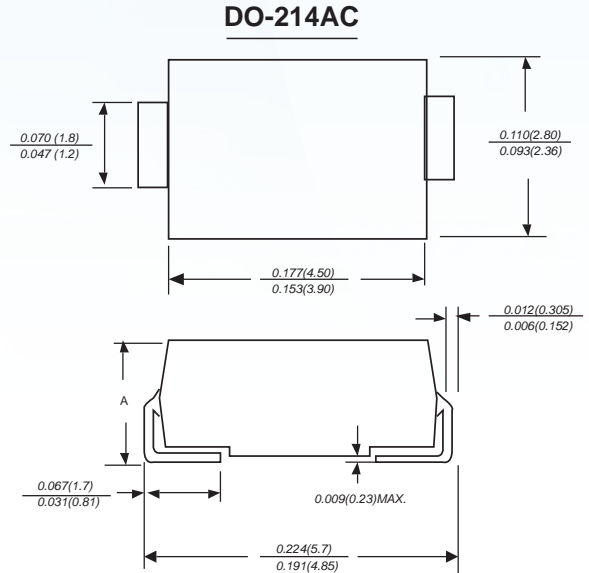
SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ For surface mounted applications
- ◆ Low reverse leakage
- ◆ Built-in strain relief, ideal for automated placement
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed: 250°C/10 seconds at terminals

MECHANICAL DATA

Case: JEDEC DO-214AC molded plastic body
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.003 ounce, 0.093 grams



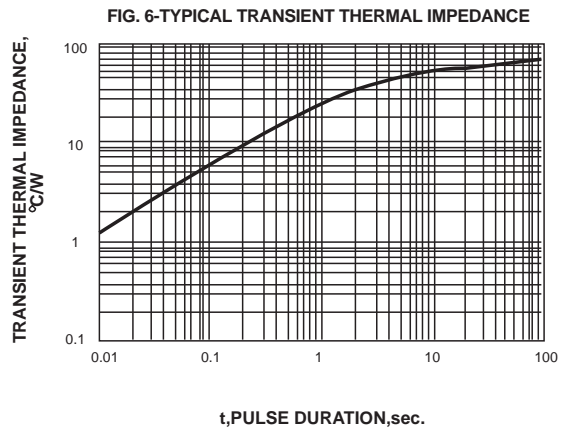
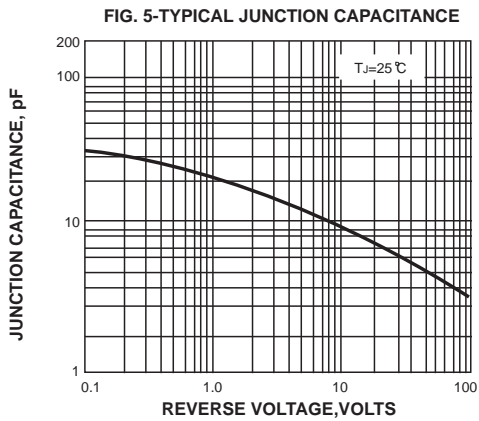
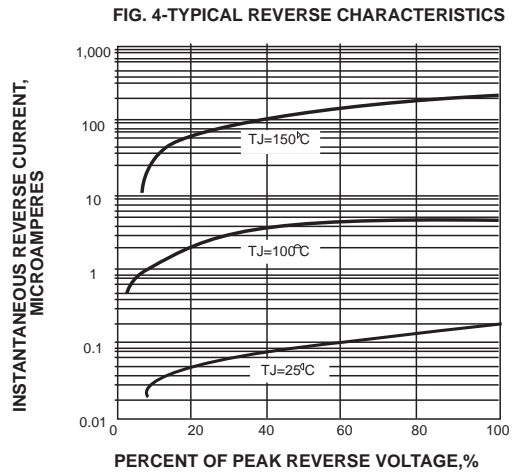
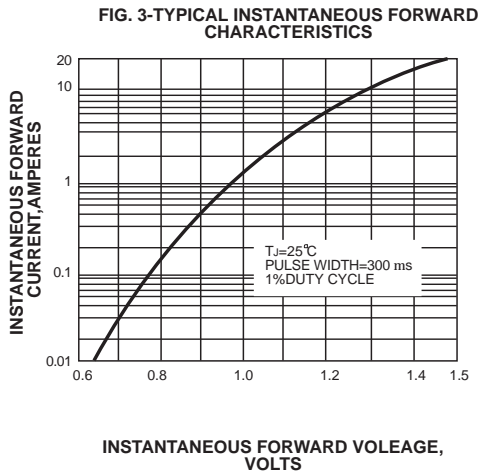
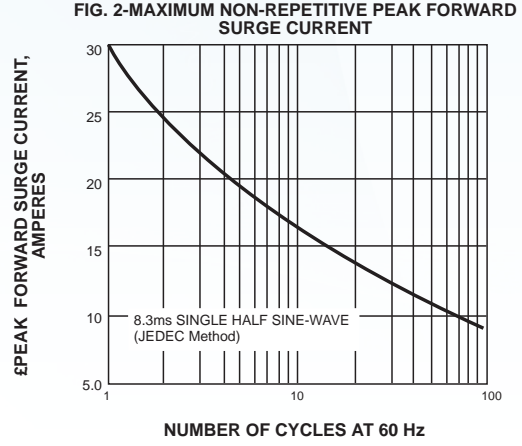
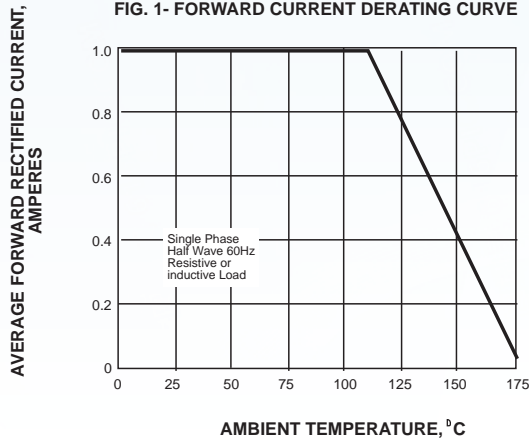
Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	GS1A	GS1B	GS1D	GS1G	GS1J	GS1K	GS1M	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_L=110^\circ\text{C}$	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	5.0 50.0							μA
Typical junction capacitance (NOTE 1)	C_J	15.0							pF
Typical thermal resistance (NOTE 2)	R_{qJA}	75.0							$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. P.C.B. mounted with 0.2x0.2" (5.0x5.0mm) copper pad areas



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